

## THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION AND NEW POWER OF ATTORNEY AND  
CHANGE OF CORRESPONDENCE ADDRESS**

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

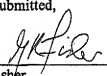
*Customer Number: 76681*

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

*Customer Number: 76681*

Respectfully submitted,

Date: 5/13/2008

  
\_\_\_\_\_  
Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

**STATEMENT UNDER 37 CFR 3.73(b)**


***MEMC Electronic Materials, Inc.***, a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in ***U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.***

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to ***MEMC Electronic Materials, Inc.*** via Assignment(s) recorded with the United States Patent and Trademark Office at the ***Reel/Frame Numbers on the attached Schedule A.***

The undersigned, ***Dr. Graham Fisher, Director of Intellectual Property***, has full authorization to act on behalf of Assignee ***MEMC Electronic Materials, Inc.***

Respectfully submitted,

Date: 5/13/2008

  
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Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

**APPENDIX A**  
**Owned by MEMC Electronic Materials, Inc.**

ATTORNEY REFERENCE	CONF. NO.	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
28744-215 (MEMC2905.16)	4312	US-2007-0169603-A1 7/26/2007	11/863,142 1/15/2007		MEMC Electronic Materials, Inc.	Division of 10/830,808 recorded at 014333/0812	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS
MEMC2905.9	1950	US-2004-0009111-A1 1/15/2004	10360,808 7/30/2003	7,162,809 2/27/2007	MEMC Electronic Materials, Inc.	014333/0812	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS
MEMC2907.1	3830	US-2003-0079573-A1 5/12/2003	10291,632 10/29/2002	6,866,713 3/15/2005	MEMC Electronic Materials, Inc.	013582/0492	SEED CRYSTALS FOR PULLING SINGLE CRYSTAL SILICON
MEMC2980.1	5778	US-2002-0104104-A1 8/12/2002	10354,829 1/22/2002	6,846,539 1/25/2005	MEMC Electronic Materials, Inc.	012789/0747	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS
MEMC2980.9	6113	US-2005-0150445 A1 7/14/2005	111005,987 1/27/2004	7,217,320 5/15/2007	MEMC Electronic Materials, Inc.	Division of 10/854,628 recorded at 012789/0747	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS
MEMC2970.1	4314	US-2003-0081985-A1 4/3/2003	10256,759 8/27/2002	7,132,091 11/7/2006	MEMC Electronic Materials, Inc.	013576/0957	SINGLE CRYSTAL SILICON INGOT HAVING A HIGH ARSENIC CONCENTRATION
MEMC2984.10	3201	US-2005-0258771-A1 11/17/2005	11174,908 7/5/2005	7,071,080 7/4/2008	MEMC Electronic Materials, Inc.	Division of 10/177,444 recorded at 013181/0822	PROCESS FOR PRODUCING SILICON ON INSULATOR STRUCTURE HAVING INTRINSIC GETTERING BY ION IMPLANTATION
MEMC2984.2	5976	US-2003-0084035-A1 1/9/2003	10777,444 6/27/2002	6,930,375 9/16/2005	MEMC Electronic Materials, Inc.	013181/0822	SILICON ON INSULATOR STRUCTURE HAVING AN EPITAXIAL LAYER AND INTRINSIC GETTERING
MEMC2982	2873	US-2003-0093659-A1 4/10/2003	06567,677 10/4/2001	6,712,673 3/30/2004	MEMC Electronic Materials, Inc.	012290/0298	POLISHING APPARATUS, POLISHING HEAD AND METHOD
MEMC3004.10	2876	US-2005-0042447-A1 3/3/2005	10983,340 10/12/2004	7,261,900 4/19/2007	MEMC Electronic Materials, Inc.	Division of 10/963,340 recorded at 013223/0124	PROCESS FOR MAKING SILICON WAFERS WITH STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS
MEMC3004.2	8328	US-2003-0138961-A1 7/9/2003	10328,481 12/23/2002	6,846,781 10/26/2004	MEMC Electronic Materials, Inc.	013233/0124	SILICON WAFERS WITH STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS AND PROCESS FOR MAKING THE SAME
MEMC3005.3	1197	US-2004-0118333-A1 6/24/2004	10699,038 10/31/2003	7,125,450 10/24/2006	MEMC Electronic Materials, Inc.	20040118333	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT
MEMC3007	2404	US-2004-0258847 A1 12/23/2004	107465,578 6/19/2003	6,942,733 9/15/2005	MEMC Electronic Materials, Inc.	013811/0117	FLUID SEALING SYSTEM FOR A CRYSTAL PULLER
28744-107 (MEMC3011.1)	9422	US-2002-0102469-A1 10/16/2002	10277,680 10/22/2002		MEMC Electronic Materials, Inc.	20030102469	PROCESS FOR CONTROLLING DENEDED ZONE DEPTH IN AN IDEAL OXYGEN PRECIPITATING SILICON WAFER
28744-138 (MEMC3003.1)	5498	US-2004-0112277-A1 6/17/2004	10705,813 08/346,655	1,119/2003	MEMC Electronic Materials, Inc.	21040112277	CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT
MEMC3043	3340		11/301/984	5,696,045 9/18/1987	MEMC Electronic Materials, Inc.	10072100380	PROCESS FOR STRIPPING OUTER EDGE OF BESOI WAFERS